

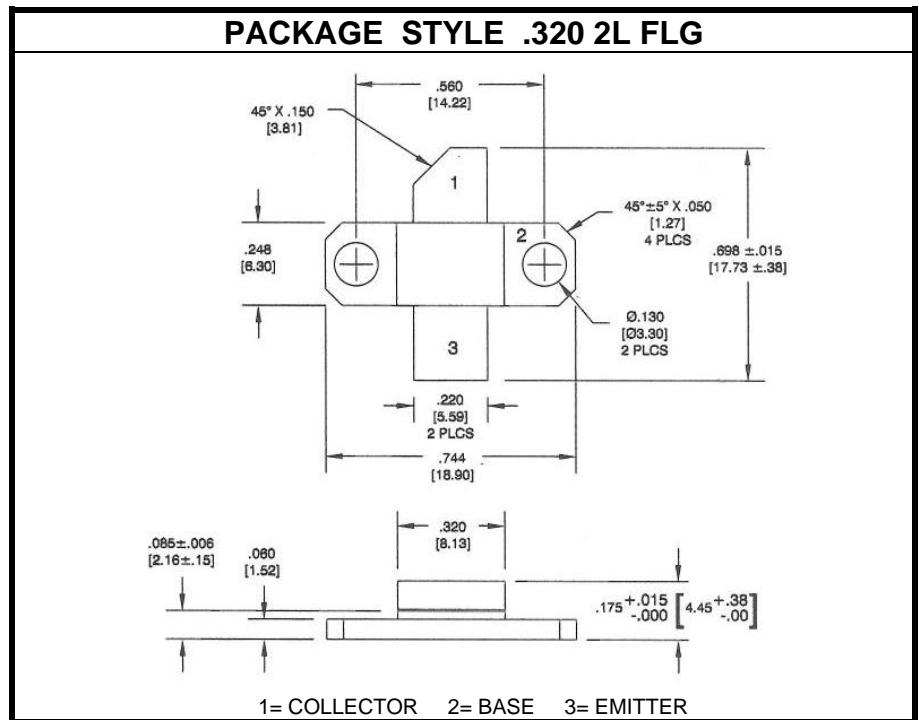
NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRA0610-23** is designed for Class C, Common Base Wideband Large Signal Amplifier Applications from 600 MHz to 1.0 GHz, With Internal Compensating Matching Network and Diffused Ballast Resistors.

MAXIMUM RATINGS

I_C	3.5 A (CONT)
V_{CES}	50 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.0 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 150 mA	50			V
BV_{EBO}	I _E = 2.0 mA	3.5			V
I_{CBO}	V _{CB} = 28 V			3.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 750 mA	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			21	pF
G_{PB}	V _{CE} = 28 V P _{out} = 23 W f = 600 MHz & 1.0 GHz	7.0			dB
η_C		50			%